FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICATION	ATTY. DOCKET NO.:13114-US-PA	APPLICATION NO.: 10/709,719
	APPLICANT: Tang	
	FILING DATE: May 25, 2004	GROUP 2818

U.S. PATENT DOUCMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	FIILNG DATE (IF APPROPRIATE)

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
		Radens et al., " A 0.135 μm^2 6F^2 Trench-Sidewall Vertical Device Cell for 4Gb/16Gb DRAM",
		2000 Symposium on VLSI Technology Digest of Technical Papers, pp. 80-81.
		Mandelman et al., " Challenges and future directions for the scaling of dynamic random-access memory
		(DRAM), in IBM J. RES. & DEV. Vol. 46 No. 2/3 March/ May 2002, pp. 187-212.

EXAMINER		DATE CONSIDERED 9/13/05

EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE
WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED.
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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

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Title of Invention	[MULTI-GATE DRAM WITH DEEP-TRENCH CAPACITOR AND FABRICATION THEREOF]

Application Number :

Confirmation Number:

First Named Applicant: Ming Tang

Attorney Docket Number: 13114-US-PA

Art Unit:

Examiner:

Search string: (6316309 or 6093614 or 6355518).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6316309	2001-11-13	Holmes, et al.		438	246
	2	6093614	2000-07-25	Gruening, et al.		438	388
	3	6355518	2002-03-12	Wu, et al.		438	246

Signature

Examiner Name	Date
	9/23/01